Renesas Electronics America Inc - R5F104LKAFA#50 Datasheet

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What is "Embedded - Microcontrollers"?

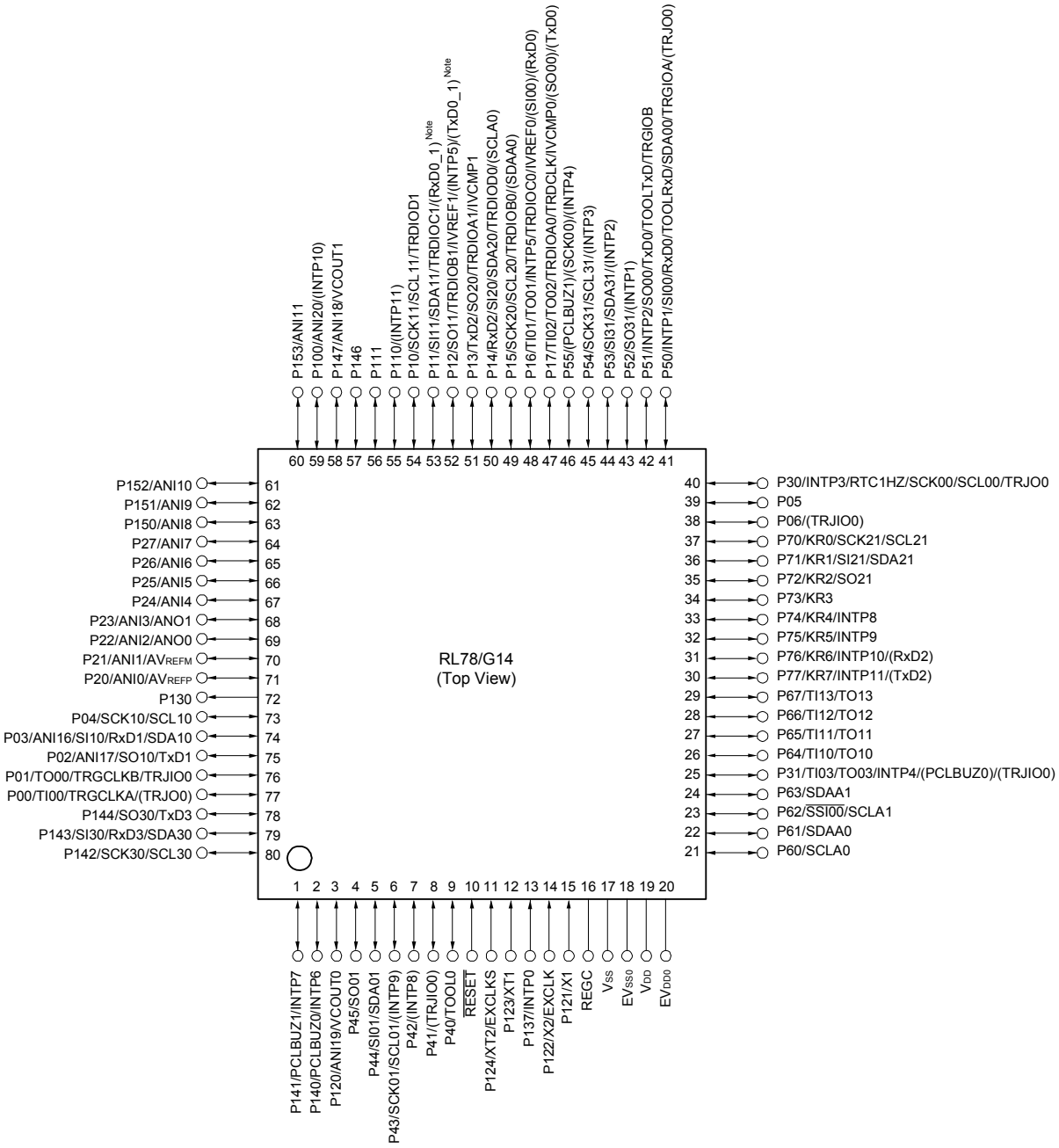
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104lkafa-50

1.3.9 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)



Note Mounted on the 384 KB or more code flash memory products.

Caution 1. Make EVSS0 pin the same potential as VSS pin.
Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.
Caution 3. Connect the REGC pin to VSS pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.
Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the VSS and EVSS0 pins to separate ground lines.
Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

(2/2)

Item		30-pin	32-pin	36-pin	40-pin
		R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)
Clock output/buzzer output		2	2	2	2
		[30-pin, 32-pin, 36-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) [40-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)			
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels
Serial interface		[30-pin, 32-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel [36-pin, 40-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels			
	I^2C bus	1 channel	1 channel	1 channel	1 channel
Data transfer controller (DTC)		28 sources			29 sources
Event link controller (ELC)		Event input: 19 Event trigger output: 7			Event input: 20 Event trigger output: 7
Vectored interrupt sources	Internal	24	24	24	24
	External	6	6	6	7
Key interrupt		—	—	—	4
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access			
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = –40 to +85°C) 1.51 ±0.06 V (T_A = –40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = –40 to +85°C) 1.50 ±0.06 V (T_A = –40 to +105°C)			
Voltage detector		1.63 V to 4.06 V (14 stages)			
On-chip debug function		Provided			
Power supply voltage		V_{DD} = 1.6 to 5.5 V (T_A = –40 to +85°C) V_{DD} = 2.4 to 5.5 V (T_A = –40 to +105°C)			
Operating ambient temperature		T_A = –40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = -40 to +105°C (G: Industrial applications)			

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

(2/2)

Item		48-pin R5F104Gx (x = K, L)	64-pin R5F104Lx (x = K, L)
Clock output/buzzer output		2	2
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
8/10-bit resolution A/D converter		10 channels	12 channels
D/A converter		2 channels	
Comparator		2 channels	
Serial interface		[48-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 2 channels • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels [64-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels	
	I^2C bus	1 channel	1 channel
Data transfer controller (DTC)		32 sources	33 sources
Event link controller (ELC)		Event input: 22 Event trigger output: 9	
Vectored interrupt sources	Internal	24	24
	External	10	13
Key interrupt		6	8
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access	
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = –40 to +85°C) 1.51 ±0.06 V (T_A = –40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = –40 to +85°C) 1.50 ±0.06 V (T_A = –40 to +105°C)	
Voltage detector		1.63 V to 4.06 V (14 stages)	
On-chip debug function		Provided	
Power supply voltage		V_{DD} = 1.6 to 5.5 V (T_A = -40 to +85°C) V_{DD} = 2.4 to 5.5 V (T_A = -40 to +105°C)	
Operating ambient temperature		T_A = -40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = -40 to +105°C (G: Industrial applications)	

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80-pin, 100-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		80-pin R5F104Mx (x = F to H, J)	100-pin R5F104Px (x = F to H, J)
Code flash memory (KB)		96 to 256	96 to 256
Data flash memory (KB)		8	8
RAM (KB)		12 to 24 Note	12 to 24 Note
Address space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)	
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz	
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f_{IH} = 32 MHz operation)	
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)	
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.	
I/O port	Total	74	92
	CMOS I/O	64	82
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)	
	Watchdog timer	1 channel	
	Real-time clock (RTC)	1 channel	
	12-bit interval timer	1 channel	
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels	
	RTC output	1 • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)	

Note In the case of the 24 KB, this is about 23 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(5/5)**

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V_I = EV_{DD0}				1	μA
	I_{LIH2}	P20 to P27, P137, P150 to P156, $\overline{RESET}$	V_I = V_{DD}				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V_I = V_{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	I_{LIL1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V_I = EV_{SS0}				-1	μA
	I_{LIL2}	P20 to P27, P137, P150 to P156, $\overline{RESET}$	V_I = V_{SS}				-1	μA
	I_{LIL3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V_I = V_{SS}	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	R_U	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V_I = EV_{SS0}, In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = 0 V)(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.80	3.09	mA
					V_{DD} = 3.0 V		0.80	3.09	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.49	2.40	
					V_{DD} = 3.0 V		0.49	2.40	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.62	2.40	
					V_{DD} = 3.0 V		0.62	2.40	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.4	1.83	
					V_{DD} = 3.0 V		0.4	1.83	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.37	1.38	
					V_{DD} = 3.0 V		0.37	1.38	
			LS (low-speed main) mode Note 7	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		260	710	μA
					V_{DD} = 2.0 V		260	710	
			LV (low-voltage main) mode Note 7	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 4	V_{DD} = 3.0 V		420	700	μA
					V_{DD} = 2.0 V		420	700	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.28	1.55	mA
					Resonator connection		0.40	1.74	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.28	1.55	
					Resonator connection		0.40	1.74	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.25	0.93	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.25	0.93	
			LS (low-speed main) mode Note 7	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		95	550	μA
					Resonator connection		140	590	
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		95	550	
					Resonator connection		140	590	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = -40°C	Square wave input		0.25	0.57	μA
					Resonator connection		0.44	0.76	
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.30	0.57	
					Resonator connection		0.49	0.76	
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.36	1.17	
					Resonator connection		0.59	1.36	
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.49	1.97	
					Resonator connection		0.72	2.16	
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		0.97	3.37	
					Resonator connection		1.16	3.56	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.18	0.51	μA
			T_A = +25°C				0.24	0.51	
			T_A = +50°C				0.29	1.10	
			T_A = +70°C				0.41	1.90	
			T_A = +85°C				0.90	3.30	

(**Notes** and **Remarks** are listed on the next page.)

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.6		mA
						V_{DD} = 3.0 V		2.6		
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.3		
						V_{DD} = 3.0 V		2.3		
			HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		5.4	10.2	mA
						V_{DD} = 3.0 V		5.4	10.2	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		5.0	9.6	
						V_{DD} = 3.0 V		5.0	9.6	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.2	7.8	
						V_{DD} = 3.0 V		4.2	7.8	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.0	7.4	
						V_{DD} = 3.0 V		4.0	7.4	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 5.0 V		3.0	5.3	
						V_{DD} = 3.0 V		3.0	5.3	
			LS (low-speed main) mode Note 5	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.4	2.3	mA
						V_{DD} = 2.0 V		1.4	2.3	
			LV (low-voltage main) mode Note 5	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.3	1.9	mA
						V_{DD} = 2.0 V		1.3	1.9	
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		3.4	6.2	mA
						Resonator connection		3.6	6.4	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		3.4	6.2	
						Resonator connection		3.6	6.4	
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		2.1	3.6	
						Resonator connection		2.2	3.7	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.6	
						Resonator connection		2.2	3.7	
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.2	2.2	mA
						Resonator connection		1.2	2.3	
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V	Normal operation	Square wave input		1.2	2.2	
						Resonator connection		1.2	2.3	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = -40°C	Normal operation	Square wave input		4.9	7.1	µA
						Resonator connection		4.9	7.1	
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		4.9	7.1	
						Resonator connection		4.9	7.1	
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		5.1	8.8	
						Resonator connection		5.1	8.8	
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		5.5	10.5	
						Resonator connection		5.5	10.5	
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		6.5	14.5	
						Resonator connection		6.5	14.5	

(**Notes** and **Remarks** are listed on the next page.)

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.79	3.32	mA
					V_{DD} = 3.0 V		0.79	3.32	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.49	2.63	
					V_{DD} = 3.0 V		0.49	2.63	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.62	2.57	
					V_{DD} = 3.0 V		0.62	2.57	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.4	2.00	
					V_{DD} = 3.0 V		0.4	2.00	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.38	1.49	
					V_{DD} = 3.0 V		0.38	1.49	
			LS (low-speed main) mode Note 7	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		250	800	µA
					V_{DD} = 2.0 V		250	800	
			LV (low-voltage main) mode Note 7	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 4	V_{DD} = 3.0 V		420	755	µA
					V_{DD} = 2.0 V		420	755	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.30	1.63	mA
					Resonator connection		0.40	1.85	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.30	1.63	
					Resonator connection		0.40	1.85	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.20	0.89	
					Resonator connection		0.25	0.97	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.20	0.89	
					Resonator connection		0.25	0.97	
			LS (low-speed main) mode Note 7	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		110	580	µA
					Resonator connection		140	630	
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		110	580	
					Resonator connection		140	630	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = -40°C	Square wave input		0.28	0.66	µA
					Resonator connection		0.47	0.85	
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.34	0.66	
					Resonator connection		0.53	0.85	
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.37	2.35	
					Resonator connection		0.56	2.54	
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.61	4.08	
					Resonator connection		0.80	4.27	
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		1.55	8.09	
					Resonator connection		1.74	8.28	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.19	0.57	µA
			T_A = +25°C				0.25	0.57	
			T_A = +50°C				0.33	2.26	
			T_A = +70°C				0.52	3.99	
			T_A = +85°C				1.46	8.00	

(**Notes** and **Remarks** are listed on the next page.)

Note 4. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $EV_{DD0} \geq V_b$.

Note 6. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 1.8 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 7. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(T_A = -40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, 1.6 V ≤ EV_{DD} = EV_{DD1} ≤ V_{DD}, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR} Note 3, Reference voltage (-) = AV_{REFM} = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	t_{CONV}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	µs
Zero-scale error Notes 1, 2	E_{ZS}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR} Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to **2.6.2 Temperature sensor characteristics/internal reference voltage characteristic**.

Note 4. When reference voltage (-) = V_{SS}, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AV_{REFM}.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings **(1/2)**

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V_{DD}		-0.5 to +6.5	V
	EV_{DD0}, EV_{DD1}	EV_{DD0} = EV_{DD1}	-0.5 to +6.5	V
	EV_{SS0}, EV_{SS1}	EV_{SS0} = EV_{SS1}	-0.5 to +0.3	V
REGC pin input voltage	V_{IREGC}	REGC	-0.3 to +2.8 and -0.3 to V_{DD} +0.3 Note 1	V
Input voltage	V_{I1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	-0.3 to EV_{DD0} +0.3 and -0.3 to V_{DD} +0.3 Note 2	V
	V_{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	V_{I3}	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, $\overline{\text{RESET}}$	-0.3 to V_{DD} +0.3 Note 2	V
Output voltage	V_{O1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-0.3 to EV_{DD0} +0.3 and -0.3 to V_{DD} +0.3 Note 2	V
	V_{O2}	P20 to P27, P150 to P156	-0.3 to V_{DD} +0.3 Note 2	V
Analog input voltage	V_{AI1}	ANI16 to ANI20	-0.3 to EV_{DD0} +0.3 and -0.3 to AV_{REF}(+) +0.3 Notes 2, 3	V
	V_{AI2}	ANI0 to ANI14	-0.3 to V_{DD} +0.3 and -0.3 to AV_{REF}(+) +0.3 Notes 2, 3	V

Note 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

Note 3. Do not exceed AV_{REF} (+) + 0.3 V in case of A/D conversion target pin.

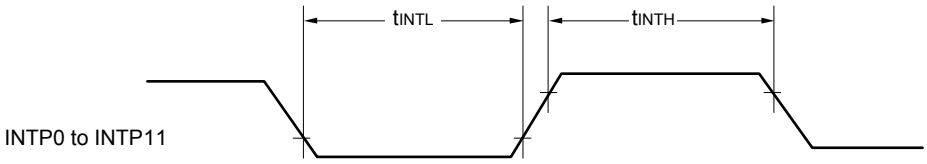
Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

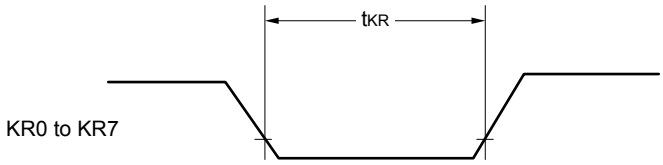
Remark 2. AV_{REF} (+): + side reference voltage of the A/D converter.

Remark 3. V_{SS}: Reference voltage

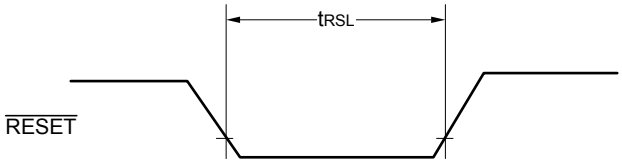
Interrupt Request Input Timing



Key Interrupt Input Timing

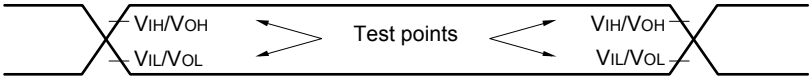


$\overline{\text{RESET}}$ Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ EV_{DD0} ≤ 5.5 V		f_{MCK}/12 Note 2	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		2.6	Mbps

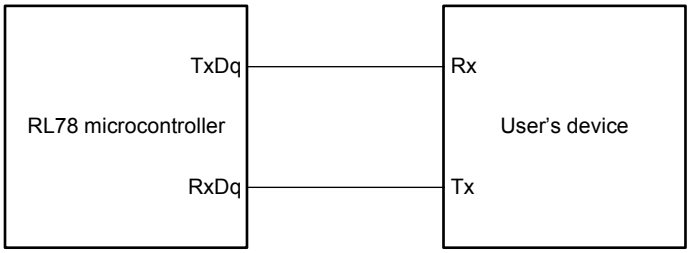
Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.
However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.
2.4 V ≤ EV_{DD0} < 2.7 V: MAX. 1.3 Mbps

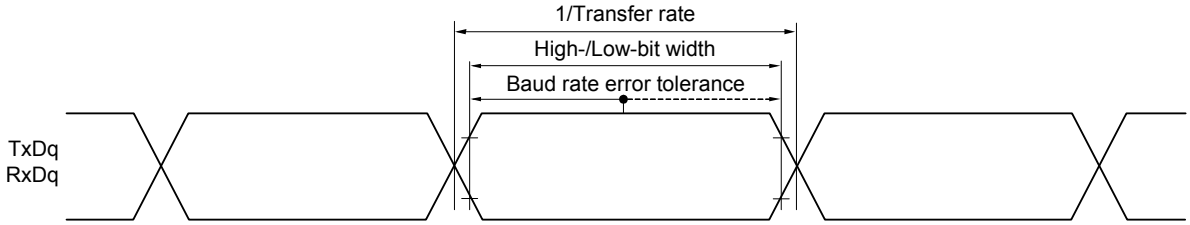
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
Transfer rate		reception	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		f_{MCK}/12 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		2.6	Mbps
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/12 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		2.6	Mbps
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/12 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.
However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.
2.4 V ≤ EV_{DD0} < 2.7 V: MAX. 1.3 Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. V_b [V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	600		ns
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000		ns
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	2300		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 150		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 340		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 916		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 24		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 36		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage / Input channel	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-)= AV_{REFM}
ANI0 to ANI14	Refer to **3.6.1 (1)**.	Refer to **3.6.1 (3)**.	Refer to **3.6.1 (4)**.
ANI16 to ANI20	Refer to **3.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **3.6.1 (1)**.		—

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +105°C, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV_{REFP} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	E_{ZS}	10-bit resolution AV_{REFP} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Full-scale error Notes 1, 2	E_{FS}	10-bit resolution AV_{REFP} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV_{REFP} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV_{REFP} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±1.5	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14		0		AV_{REFP}	V
		Internal reference voltage output (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} Note 4			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} Note 4			V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

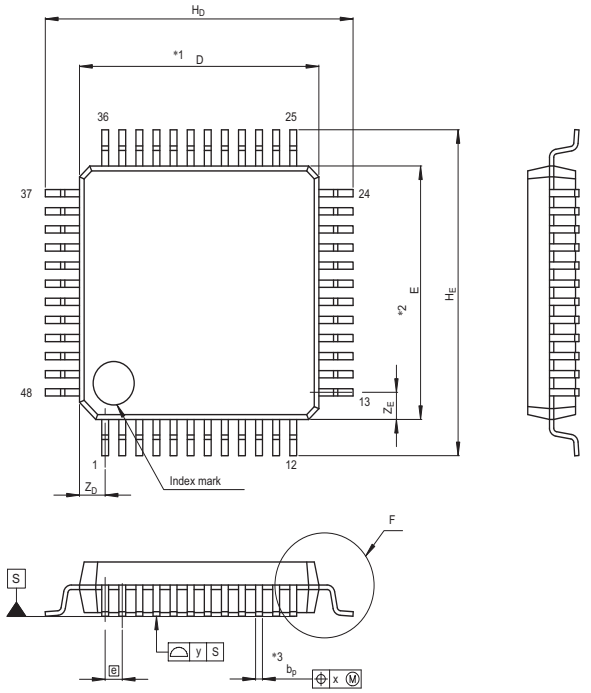
Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.

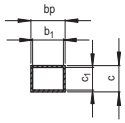
Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Note 4. Refer to **3.6.2 Temperature sensor characteristics/internal reference voltage characteristic**.

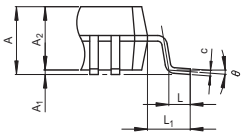
R5F104GKAFB, R5F104GLAFB
R5F104GKGFB, R5F104GLGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP48-7x7-0.50	PLQP0048KB-A	48P6Q-A	0.2g





Terminal cross section



Detail F

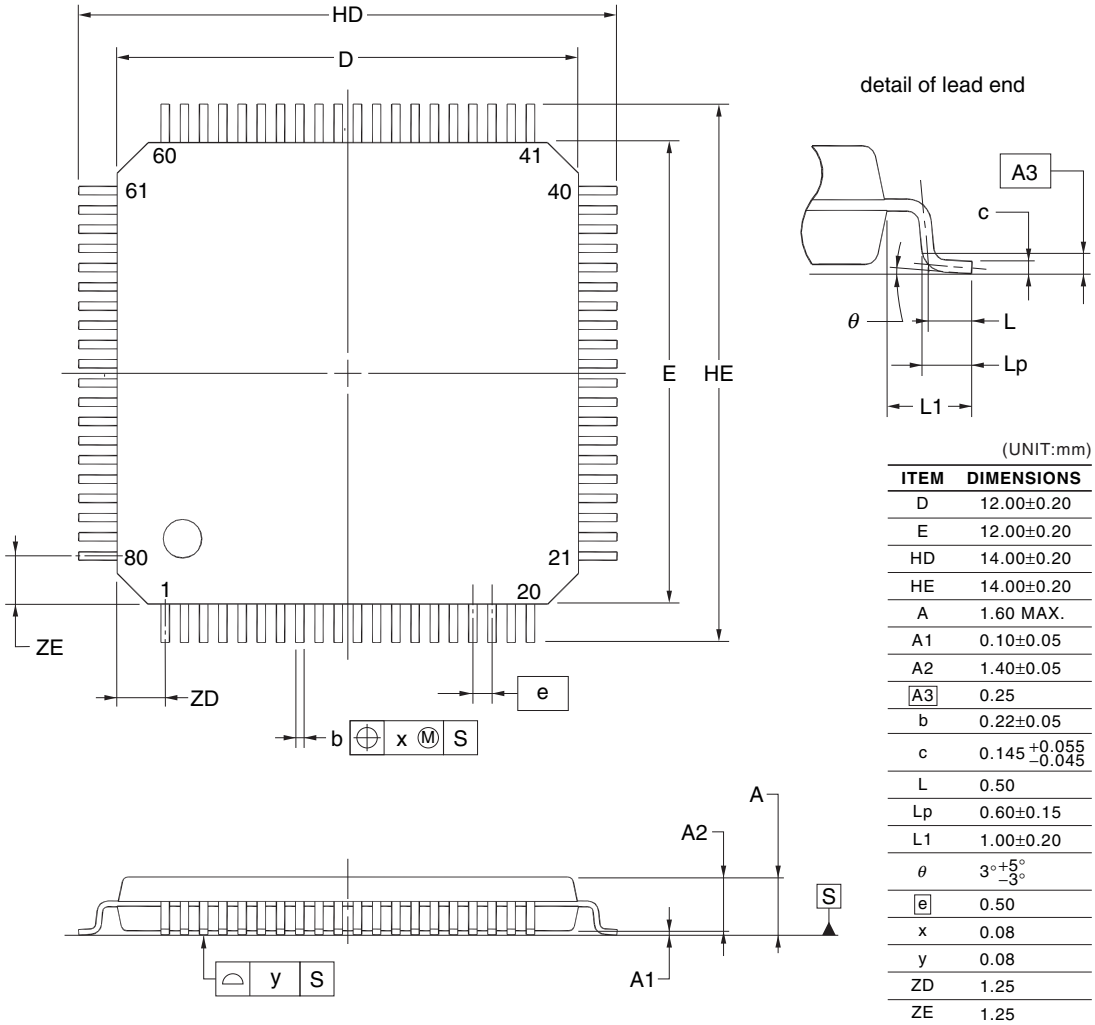
NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

4.9 80-pin products

R5F104MFAFB, R5F104MGAFB, R5F104MHAFB, R5F104MJAFB
R5F104MFDFB, R5F104MGDFB, R5F104MHDFB, R5F104MJDFB
R5F104MFGFB, R5F104MGGFB, R5F104MHGFB, R5F104MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53



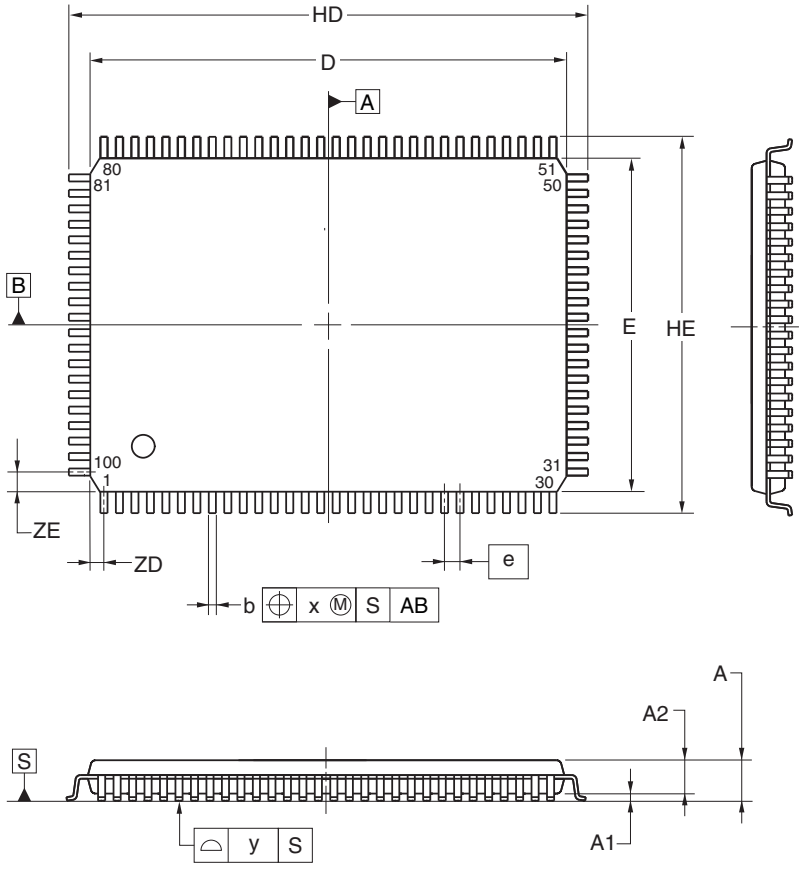
(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.50
x	0.08
y	0.08
ZD	1.25
ZE	1.25

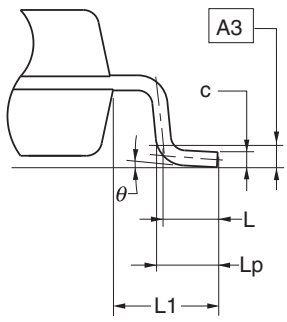
NOTE
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

R5F104PFAFA, R5F104PGAFA, R5F104PHAFA, R5F104PJAFA
R5F104PFDFA, R5F104PGDFA, R5F104PHDFA, R5F104PJDFA
R5F104PFGFA, R5F104PGGFA, R5F104PHGFA, R5F104PJGFA
R5F104PKAFA, R5F104PLAFA
R5F104PKGFA, R5F104PLGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.32^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.65
x	0.13
y	0.10
ZD	0.575
ZE	0.825

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